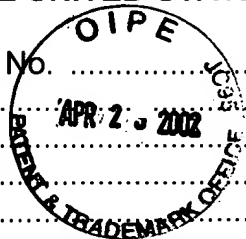


9/13 Amdt
S-7-02
A. Walk

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 09/754,926
Filing Date 1/4/01
Inventor Ahn et al.
Assignee Micron Technology, Inc.
Group Art Unit 2813
Examiner E. Kielin
Attorney's Docket No. MI22-1533
Title: Methods of Forming Assemblies Comprising Silicon-Doped Aluminum Oxide



RESPONSE TO FEBRUARY 27, 2002 OFFICE ACTION

To: Assistant Commissioner for Patents
Washington, D.C. 20231

From: David G. Latwesen (Tel. 509-624-4276; Fax 509-838-3424)
Wells St. John P.S.
601 W. First Avenue, Suite 1300
Spokane, WA 99201-3828

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APR 29 2002
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AMENDMENTS

In the Specification

Please replace the title with:

--Methods of Forming Assemblies Comprising Silicon-Doped Aluminum Oxide--

Please replace the paragraph beginning at line 22 of page 1 with the following clean replacement paragraph in accordance with 37 C.F.R. § 1.121(b)(1)(ii):

--Of the listed high-k materials, aluminum oxide has received significant interest.

Aluminum oxide has been used as a high-k inter-poly dielectric (IPD) for low voltage/high speed flash memories. Specifically, it has been shown that 10 nanometer thick Al₂O₃, with